

140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor24 January 2014Product data sheet

1. General description

PNP high-voltage low V_{CEsat} Breakthrough Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- AEC-Q101 qualified

3. Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-140	V
I _C	collector current			-	-	-4	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-10	А
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	100	150	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1
3	E	emitter		· •
4	С	collector	☐1	3 sym028

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PBHV9414Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBHV9414Z	V9414Z

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-180	V
V _{CEO}	collector-emitter voltage	open base		-	-140	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-4	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-10	А
I _B	base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C

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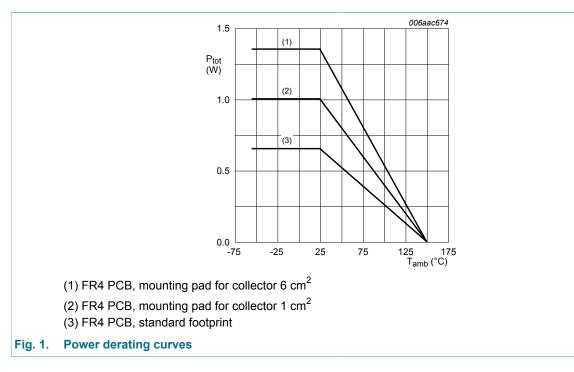
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Symbol	Parameter	Conditions	Min	Мах	Unit
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



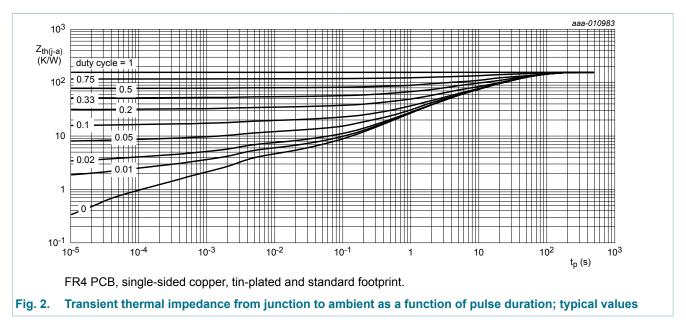
9. Thermal characteristics

Table 6. The	Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance	in free air	[1]	-	-	192	K/W	
		[2]	-	-	125	K/W		
	ambient		[3]	-	-	93	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

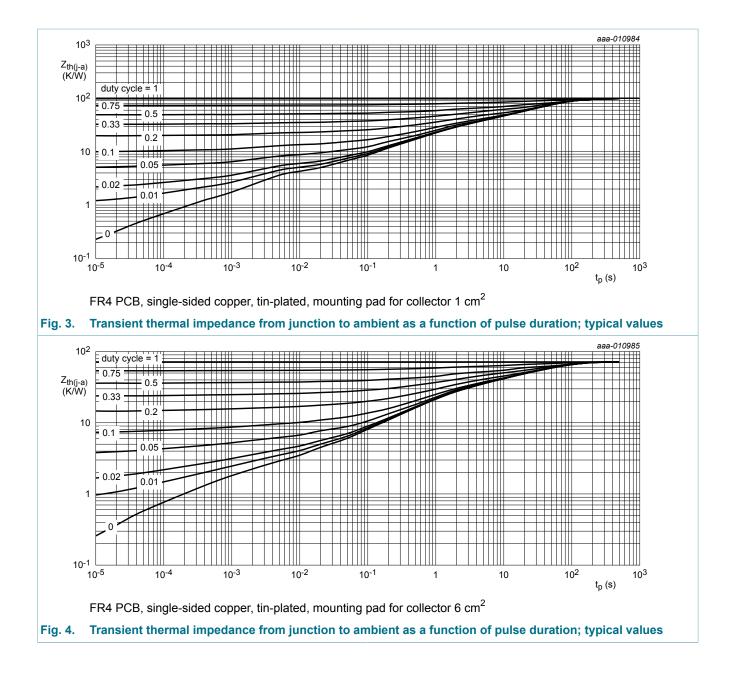
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².





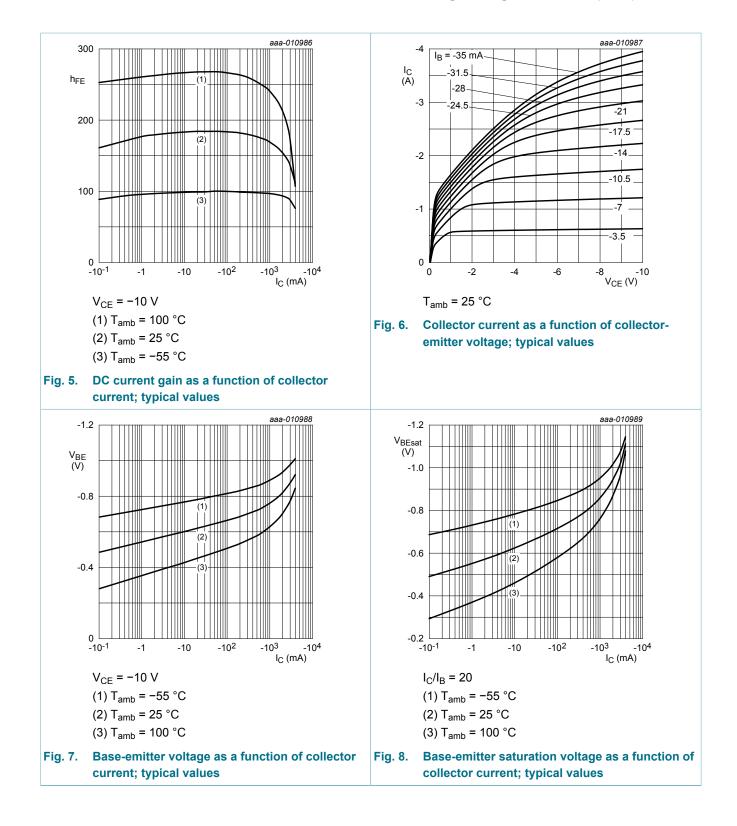
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -150 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -150 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -115 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -6 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I _C = -10 mA; T _{amb} = 25 °C	100	160	-	
		$V_{CE} = -5 \text{ V; } I_C = -1 \text{ A; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	100	150	300	
		V_{CE} = -5 V; I _C = -3 A; pulsed; t _p ≤ 300 µs; $\bar{\delta}$ ≤ 0.02 ; T _{amb} = 25 °C	75	100	-	
		V_{CE} = -5 V; I _C = -4 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	35	50	-	
V _{CEsat} collector-emitter saturation voltage		I_{C} = -100 mA; I_{B} = -5 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-45	-60	mV
		I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-60	-100	mV
		$\begin{split} & \textbf{I}_{C} = -1 \text{ A}; \text{ I}_{B} = -100 \text{ mA}; \text{ pulsed}; \\ & \textbf{t}_{p} \leq 300 \mu\text{s}; \delta \leq 0.02 ; \textbf{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-100	-150	mV
		I_{C} = -3 A; I_{B} = -300 mA; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	-	-275	-370	mV
		I_{C} = -4 A; I_{B} = -400 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-420	-550	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	100	150	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -5 V; I _C = -1 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C; pulsed	-	-	-1.1	V

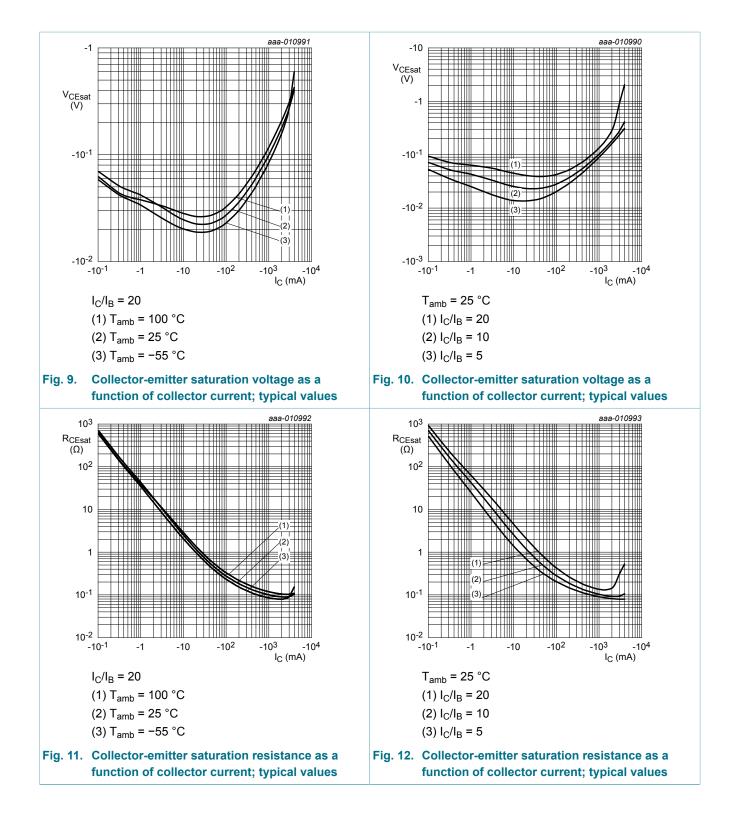
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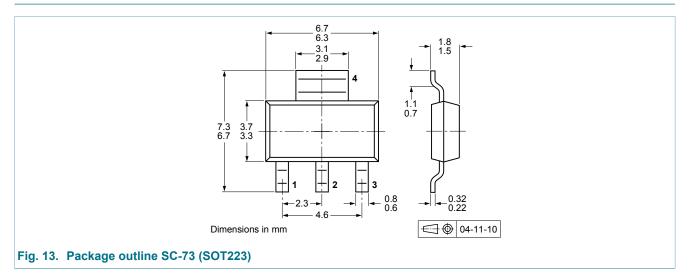
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11. Test information

11.1 Quality information

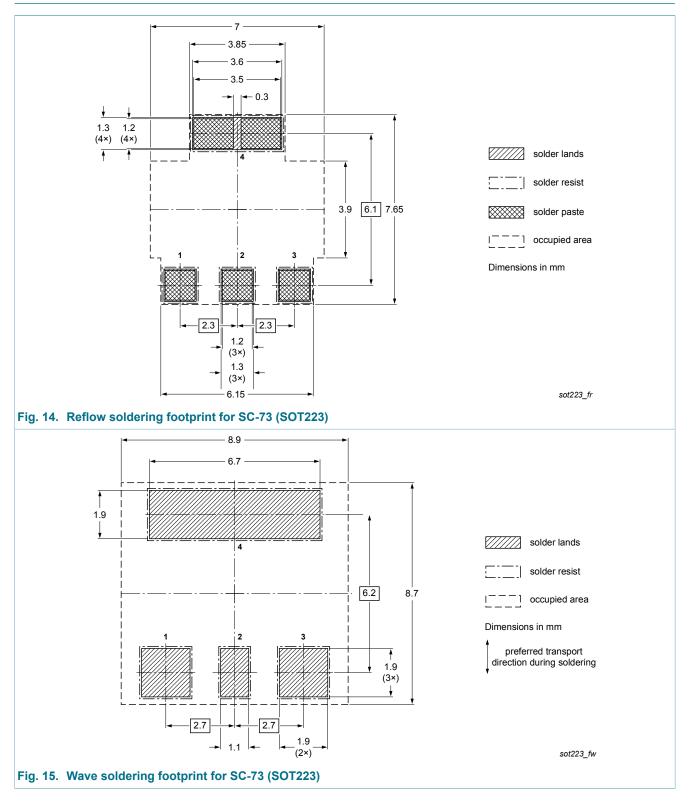
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBHV9414Z v.2	20140124	Product data sheet	-	PBHV9414Z v.1		
Modifications:	Product status char	nged	·			
PBHV9414Z v.1	20131001	Objective data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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